

Abstract

BONDING WIRE FOR SEMICONDUCTOR DEVICE

The present invention provides a bonding wire capable of simultaneously satisfying ball bonding reliability and wedge bondability required of bonding wires for memories, the bonding wire including a core material containing one or more of Ga, In, and Sn for a total of 0.1 to 3.0 at% with a balance being made up of Ag and incidental impurities; and a coating layer formed over a surface of the core material, containing one or more of Pd and Pt, or Ag and one or more of Pd and Pt, with a balance being made up of incidental impurities, wherein the coating layer is 0.005 to 0.070 μm in thickness.